

Amendments to the Claims:

The following listing of claims replaces all other versions of claims previously presented.

Listing of Claims:

1-36 (Canceled)

37 (New): A semiconductor device comprising:

a plurality of bonding pads, wherein each of the bonding pads has a first metal and a plurality of second metals, each of the plurality of second metals has a linear shape, is arranged under the first metal, and is connected with the first metal; and

a passivation film which covers a side wall and a top surface of the first metal of each of the plurality of bonding pads and has a plurality of openings, each of the plurality of openings exposing a part of the top surface of the first metal of each of the plurality of bonding pads,

wherein in plan view, the bonding pads are arranged in order and on a long side direction of the second metal.

38 (New): The semiconductor device according to claim 37, wherein width W and interval D of a bottom of the second metals satisfy a relation:

$$W \leq D \leq 2W.$$

39 (New): The semiconductor device according to claim 37, wherein each of the plurality of bonding pads has a third metal arranged under the plurality of second metals and is connected with the plurality of second metals, and

wherein the first metal is composed of aluminum and each of the plurality of second metals is composed of tungsten.

40 (New): The semiconductor device according to claim 37, wherein in plan view, an input buffer and an output buffer are formed below each of the plurality of bonding pads, each of the input buffer and the output buffer including a transistor, the input buffer receiving a first

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signal from the bonding pad and outputting the first signal to an internal circuit, the output buffer receiving a second signal from the internal circuit and outputting the second signal to the bonding pad.

41 (New): The semiconductor device according to claim 37, wherein the first metal and each of the plurality of bonding pads is probed by a probe needle in a direction perpendicular to the long side direction of the second metals.